

**Product data sheet** 

## 1. Product profile

### 1.1 General description

NPN silicon planar epitaxial transistor in a 4-pin dual-emitter SOT343R plastic package.

### 1.2 Features and benefits

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability

### 1.3 Applications

- Intended for Radio Frequency (RF) front end applications in the GHz range, such as:
  - analog and digital cellular telephones
  - cordless telephones (Cordless Telephone (CT), Personal Communication Network (PCN), Digital Enhanced Cordless Telecommunications (DECT), etc.)
  - radar detectors
  - pagers
  - ◆ Satellite Antenna TeleVision (SATV) tuners

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{CBO}}$	collector-base voltage	open emitter	-	-	15	V
$V_{CEO}$	collector-emitter voltage	open base	-	-	6	V
I <sub>C</sub>	collector current (DC)		-	-	10	mA
P <sub>tot</sub>	total power dissipation	$T_{sp} \le 145  ^{\circ}C$	<u>[1]</u> -	-	60	mW
h <sub>FE</sub>	DC current gain	$I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V};$ $T_j = 25 \text{ °C}$	60	100	200	
C <sub>CBS</sub>	collector-base capacitance	$V_{CB} = 5 \text{ V}; f = 1 \text{ MHz};$ emitter grounded	-	0.17	0.3	pF
f <sub>T</sub>	transition frequency	$I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V};$ f = 1 GHz; $T_{amb} = 25 \text{ °C}$	-	14	-	GHz



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
MSG	maximum stable gain	$I_C = 5$ mA; $V_{CE} = 3$ V; f = 1.8 GHz; $T_{amb} = 25$ °C	-	18	-	dB
$ s_{21} ^2$	insertion power gain	$I_{C} = 5 \text{ mA}; V_{CE} = 3 \text{ V};$ $f = 1.8 \text{ GHz}; T_{amb} = 25 \text{ °C};$ $Z_{S} = Z_{L} = 50 \Omega$	-	14	-	dB
NF	noise figure	$\Gamma_{\text{S}} = \Gamma_{\text{opt}}; \ I_{\text{C}} = 1 \text{ mA}; \ V_{\text{CE}} = 3 \text{ V}; \ f = 2 \text{ GHz}$	-	1	-	dB

<sup>[1]</sup>  $T_{sp}$  is the temperature at the soldering point of the collector pin.

# 2. Pinning information

Table 2. Pinning

	3		
Pin	Description	Simplified outline	Symbol
1	collector		
2	emitter	3 4	1 
3	base		3 —
4	emitter		' `
		2 1	2, 4 sym086

# 3. Ordering information

Table 3. Ordering information

Type number	Package	Package			
	Name	Description	Version		
BFG310W/XR	-	plastic surface mounted package; reverse pinning; 4 leads	SOT343R		

## 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
BFG310W/XR	A7*

[1] \* = p: made in Hong Kong.

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	15	V
$V_{CEO}$	collector-emitter voltage	open base	-	6	V
$V_{EBO}$	emitter-base voltage	open collector	-	2	V
I <sub>C</sub>	collector current (DC)		-	10	mA
P <sub>tot</sub>	total power dissipation	$T_{sp} \le 145  ^{\circ}C$	<u>[1]</u> _	60	mW
T <sub>stg</sub>	storage temperature		-65	+175	°C
Tj	junction temperature		-	175	°C

<sup>[1]</sup>  $T_{sp}$  is the temperature at the soldering point of the collector pin.

### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	$T_{sp} \le 145  ^{\circ}C$	<u>[1]</u> 530	K/W

<sup>[1]</sup>  $T_{sp}$  is the temperature at the soldering point of the collector pin.

## 7. Characteristics

Table 7. Characteristics

 $T_i = 25$  °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$I_{CBO}$	collector-base cut-off current	$I_E = 0 \text{ A}; V_{CB} = 6 \text{ V}$	-	-	15	nA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 5 mA; V <sub>CE</sub> = 3 V	60	100	200	
$C_{CBS}$	collector-base capacitance	V <sub>CB</sub> = 5 V; f = 1 MHz; emitter grounded	-	0.17	0.3	pF
C <sub>CES</sub>	collector-emitter capacitance	$V_{CE} = 5 \text{ V}$ ; f = 1 MHz; base grounded	-	0.22	-	pF
$C_{EBS}$	emitter-base capacitance	V <sub>EB</sub> = 0.5 V; f = 1 MHz; collector grounded	-	0.16	-	pF
f <sub>T</sub>	transition frequency	$I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V}; f = 1 \text{ GHz};$ $T_{amb} = 25 ^{\circ}\text{C}$	-	14	-	GHz
MSG	maximum stable gain	$I_C = 5$ mA; $V_{CE} = 3$ V; $f = 1.8$ GHz; $T_{amb} = 25$ °C	-	18	-	dB
$ s_{21} ^2$	insertion power gain	$I_C$ = 5 mA; $V_{CE}$ = 3 V; $T_{amb}$ = 25 °C; $Z_S$ = $Z_L$ = 50 $\Omega$				
		f = 1.8 GHz	-	14	-	dB
		f = 3 GHz	-	11	-	dB
NF	noise figure	$\Gamma_{\text{S}} = \Gamma_{\text{opt}}$ ; $I_{\text{C}} = 1$ mA; $V_{\text{CE}} = 3$ V; $f = 2$ GHz	-	1	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	$I_C = 5$ mA; $V_{CE} = 3$ V; $f = 1.8$ GHz; $T_{amb} = 25$ °C; $Z_S = Z_L = 50$ $\Omega$	-	1.8	-	dBm
IP3	third order intercept point	$I_{C}$ = 5 mA; $V_{CE}$ = 3 V; f = 1.8 GHz; $T_{amb}$ = 25 °C; $Z_{S}$ = $Z_{L}$ = 50 $\Omega$	-	8.5	-	dBm

BFG310W\_XR

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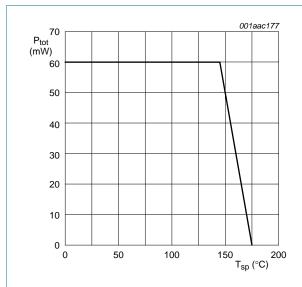


Fig 1. Power derating curve

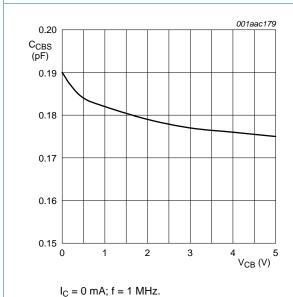


Fig 3. Collector-base capacitance as a function of collector-base voltage; typical values

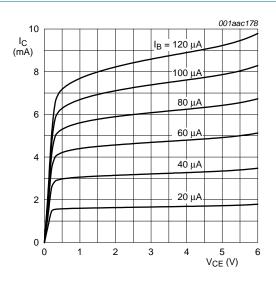
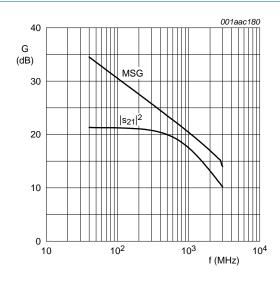


Fig 2. Collector current as a function of collector-emitter voltage; typical values



 $I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V}.$ 

Fig 4. Gain as a function of frequency; typical values

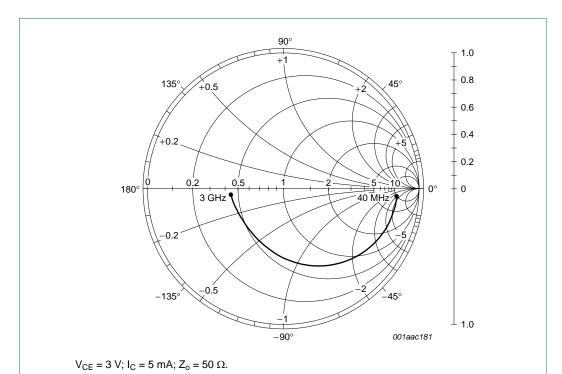


Fig 5. Common emitter input reflection coefficient (s<sub>11</sub>); typical values

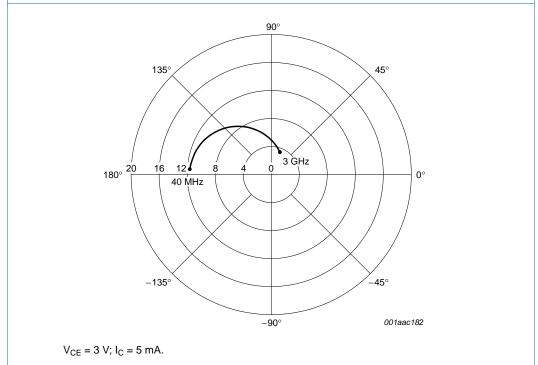


Fig 6. Common emitter forward transmission coefficient (s<sub>21</sub>); typical values

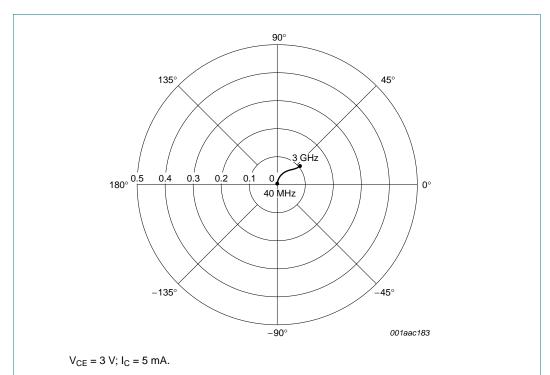


Fig 7. Common emitter reverse transmission coefficient (s<sub>12</sub>); typical values

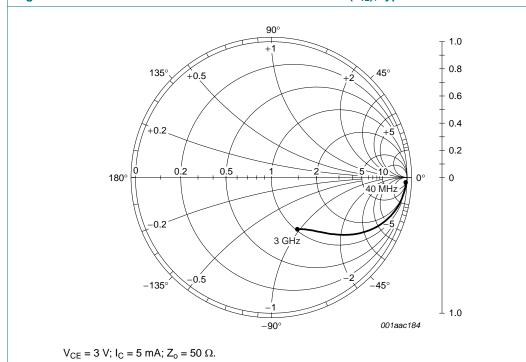


Fig 8. Common emitter output reflection coefficient (s<sub>22</sub>); typical values

# 8. Application information

Table 8. SPICE parameters of the BFG310W DIE

Sequence	Parameter	Value	Unit
1	IS	16.17	аА
2	BF	210	-
3	NF	1	-
4	VAF	50	V
5	IKF	59.83	mA
6	ISE	1.726	fA
7	NE	2.114	-
8	BR	6	-
9	NR	1	-
10	VAR	2.3	V
11	IKR	10	A
12	ISC	0	аА
13	NC	1.5	-
14	RB	3.6	Ω
15	RE	2.1	Ω
16	RC	1.6	Ω
17	CJE	115.6	fF
18	VJE	866.3	mV
19	MJE	0.285	-
20	CJC	68.18	fF
21	VJC	601	mV
22	MJC	0.123	-
23	XCJC	1	-
24	FC	0.7	-
25	TF	8.3	ps
26	XTF	10	-
27	VTF	1000	V
28	ITF	150	mA
29	PTF	0	deg
30	TR	0	ns
31	KF	0	-
32	AF	1	-
33	TNOM	25	°C
34	EG	1.014	eV
35	XTB	0	-
36	XTI	8	-
37	Q1.AREA	1	-

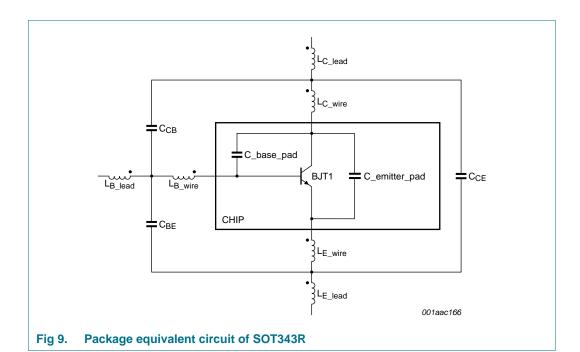


Table 9. List of components; see Figure 9

Designation	Value	Unit
C <sub>CB</sub>	2	fF
C <sub>BE</sub>	80	fF
C <sub>CE</sub>	80	fF
C_base_pad	67	fF
C_emitter_pad	142	fF
L <sub>C_wire</sub>	0.767	nH
L <sub>B_wire</sub>	0.842	nH
L <sub>E_wire</sub>	0.212	nH
L <sub>C_lead</sub>	0.28	nH
L <sub>B_lead</sub>	0.281	nH
L <sub>E_lead</sub>	0.1	nH

## 9. Package outline

### Plastic surface-mounted package; reverse pinning; 4 leads

SOT343R

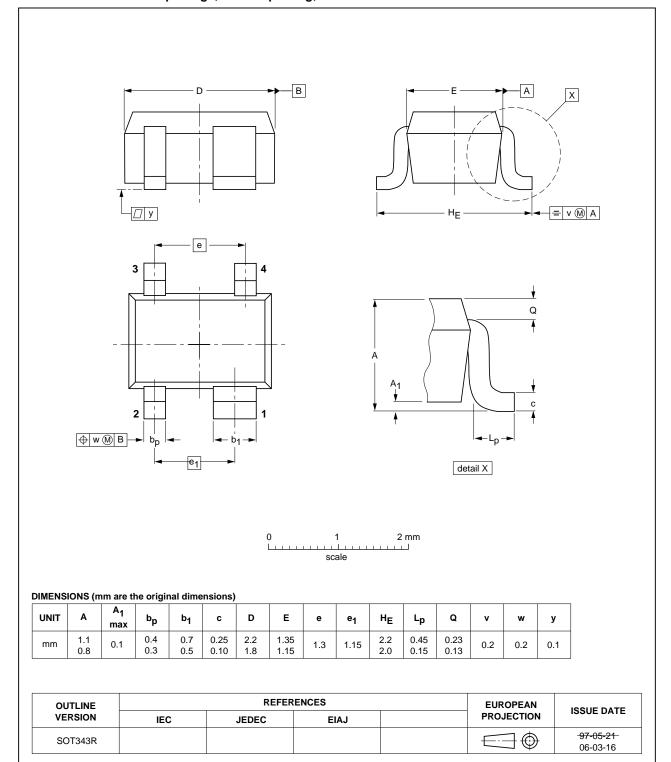


Fig 10. Package outline SOT343R

# 10. Revision history

### Table 10. Revision history

Release date	Data sheet status	Change notice	Supersedes
20110915	Product data sheet	-	BFG310W_XR v.1
<ul> <li>The format of this data sheet has been redesigned to comply with the new identit guidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>			ere appropriate.
i ackage of	dillie diawings have been d	ipuated to the latest vers	51011.
20050202	Product data sheet	-	-
	20110915  The format guidelines of Legal texts Package of	<ul> <li>20110915 Product data sheet</li> <li>The format of this data sheet has been guidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the r</li> <li>Package outline drawings have been upon the results of the results of</li></ul>	Product data sheet     The format of this data sheet has been redesigned to comply we guidelines of NXP Semiconductors.     Legal texts have been adapted to the new company name wheele Package outline drawings have been updated to the latest version.

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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# BFG310W/XR

### **NPN 14 GHz wideband transistor**

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